



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Lin, et al. Docket No.: TSM02-1369
Serial No.: 10/650,445 Art Unit: 2811
Filed: August 28, 2003 Examiner: TBD
For: Ultra-Thin Body Transistor with Recessed Silicide Contacts

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Combined Form PTO/SB/08a and 08b (1 page) citing (6) references
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Respectfully submitted,

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Commissioner for Patents
P. O. Box 1450
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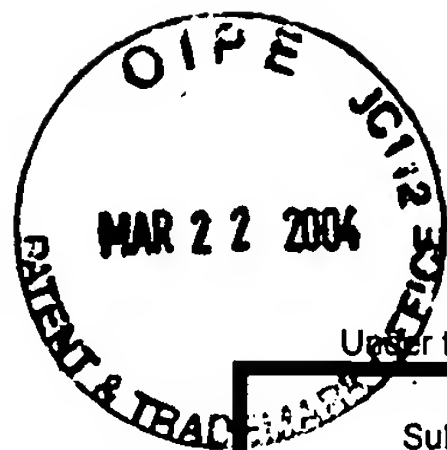
Respectfully submitted,

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March 17, 2004

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/650,445
Filing Date	8/28/2003
First Named Inventor	Lin, et al.
Art Unit	2811
Examiner Name	TBD
Attorney Docket Number	TSM02-1369

Sheet 1 of 1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
	1	US-4,998,510	03-12-1991	Rognon	
	2	US-6,137,149	10-24-2000	Kodama	
	3	US-6,420,218 B1	07-16-2002	Yu	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	4	Chau, R., et al., "A 50nm Depleted-Substrate CMOS Transistor (DST)," IEDM, pp. 621-624, 2001.	
	5	Choi, Y.K., et al., "Ultrathin-Body SOI MOSFET for Deep-Sub-Tenth Micron Era," IEEE Electron Device Letters, Vol. 21, No. 5, pp. 254-255, May 2000.	
	6	Yeo, Y.C., et al., "Design and Fabrication of 50-nm Thin-Body p-MOSFETs with a SiGe Heterostructure Channel," IEEE Transactions on Electron Devices, Vol. 49, No. 2, pp. 279-286, February 2002.	

Examiner Signature		Date Considered	
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